1.8V Drive Nch MOSFET RUM003N02

Structure

Silicon N-channel MOSFET

Applications

Switching

Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Low voltage drive (1.8V) makes this device ideal for portable equipment.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.

Packaging specifications

Туре	Package	Taping
	Code	T2L
	Basic ordering unit (pieces)	8000
RUM00	0	

•Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit			
Drain-source voltage		Vdss	20	V			
Gate-source voltage		Vgss	±8	V			
	Continuous	lo	±300	mA			
Drain current	Pulsed	DP ^{*1}	±600	mA			
Total power dissipation		Po ^{*2}	150	mW			
Channel temperature		Tch	150	°C			
Range of storage temperature		Tstg	-55 to +150	°C			

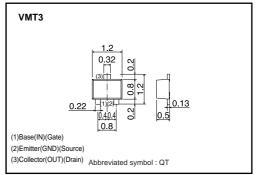
∗1 Pw≤10µs, Duty cycle≤1%

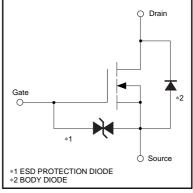
*2 Each terminal mounted on a recommended land

Thermal resistance

Parameter	Symbol	Limits	Unit	
Channel to ambient	Rth(ch-a)*	833	°C / W	
* Each terminal mounted on a recommended land				

•Dimensions (Unit : mm)







Equivalent circuit

Transistor

•Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	lgss	-	_	10	μΑ	Vgs=±8V, Vds=0V
Drain-source breakdown voltage	V(BR)DSS	20	-	-	V	ID=1mA, VGs=0V
Zero gate voltage drain current	Idss	-	-	1.0	μA	VDS=20V, VGS=0V
Gate threshold voltage	VGS(th)	0.3	-	1.0	V	Vds=10V, Id=1mA
		-	0.7	1.0	Ω	ID=300mA, Vgs=4.0V
Static drain-source on-state resistance	RDS(on)*	-	0.8	1.2	Ω	ID=300mA, Vgs=2.5V
		-	1.0	1.4	Ω	ID=300mA, Vgs=1.8V
Forward transfer admittance	Y _{fs} *	400	-	-	ms	ID=300mA, VDs=10V
Input capacitance	Ciss	-	25	-	pF	VDS=10V
Output capacitance	Coss	-	10	-	pF	Vgs=0V
Reverse transfer capacitance	Crss	-	10	-	pF	f=1MHz
Turn-on delay time	td(on) *	-	5	-	ns	I⊳=150mA, V⊳⊳ ≒10V
Rise time	tr *	-	10	-	ns	Vgs=4.0V
Turn-off delay time	td(off) *	-	15	-	ns	R∟=67Ω
Fall time	tr *	-	10	_	ns	Rg=10Ω
* Pulsod						

* Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

-	•	,		,		
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd *	-	-	1.2	V	Is= 100mA, V _{GS} =0V
* Pulsed						

•Electrical characteristic curves

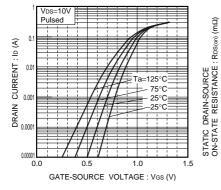


Fig.1 Typical transfer characteristics

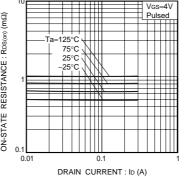


Fig.2 Static drain-source on-state resistance vs. drain current (I)

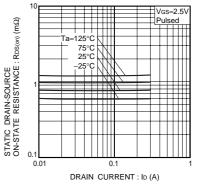
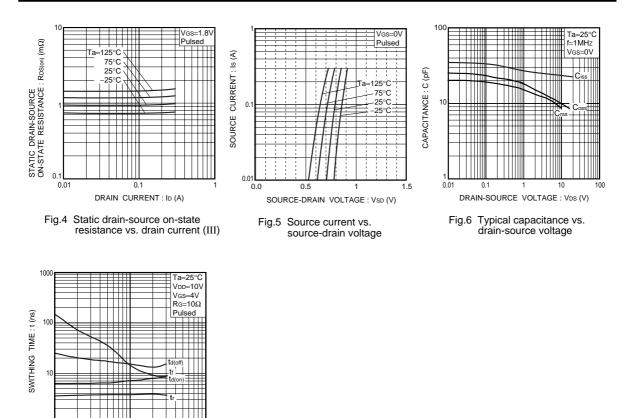


Fig.3 Static drain-source on-state resistance vs. drain current (II)

RUM003N02

Transistor



DRAIN CURRENT : ID (A) Fig.7 Switching characteristics

0.1

1 0.01

•Switching characteristics measurement circuit

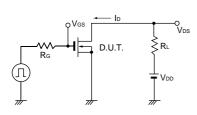


Fig.8 Switching time measurement circuit

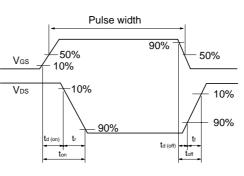


Fig.9 Switching time waveforms

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